

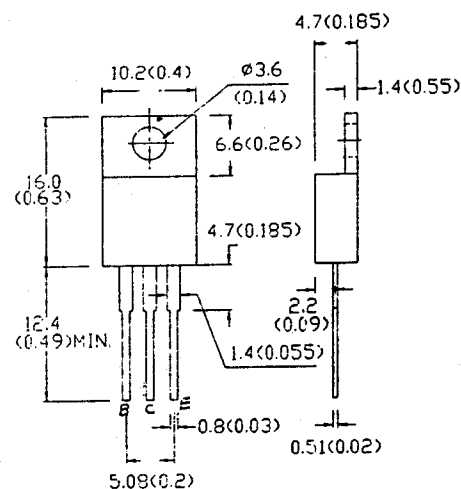
DESCRIPTION

BD437 is silicon epitaxial-base NPN power transistor, intended for use in medium power linear and switching applications.

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage
Collector-Emitter Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Collector Current
Collector Peak Current ($t < 10\text{ms}$)
Continuous Power Dissipation
Operating & Storage Junction Temperature

VCBO 45V
VCES 45V
VCEO 45V
VEBO 5V
IC 4A
ICM 7A
Pd 36W
Tj, Tstg -65 to +150°C



ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Collector Cutoff Current	ICBO			100	μA	VCB=45V IE=0
Collector Cutoff Current	ICES			100	μA	VCE=45V VBE=0
Emitter Cutoff Current	IEBO			1	mA	VEB=5V IC=0
Collector-Emitter Breakdown Voltage	LVCEO*	45			V	IC=10mA IB=0
Collector-Emitter Saturation Voltage	VCE(sat)*			0.6	V	IC=2A IB=0.2A
Base-Emitter Voltage	VBE*			1.2	V	IC=2A VCE=1V
D.C. Current Gain	HFE*	30	130			IC=10mA VCE=5V
		85	140			IC=500mA VCE=1V
		40				IC=2A VCE=1V
Current Gain Bandwidth Product	fT*	3			MHz	IC=250mA VCE=1V

* Pulse Test : Pulse Width <300μs, Duty Cycle <2%.



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